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Alessandro Callegari, et al.

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AC	5,312,565	11/01	Misra, et al.			
	6,037,003	3/14/00	Gordon, et al.			
	5,728,222	3/17/98	Barbee, et al.			
	5,648,113	7/15/97	Barbee, et al.			
	5,540,777	7/30/96	Barbee, et al.			
	5,431,734	7/11/95	Chapple-Sokol, et al.			
AC	4,097,314	6/27/78	Schlesier, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AC		Eble, R., et al., "Low Temperature Aluminum Oxide Deposition Using Trimethylaluminum", <u>Journal of Electronic Materials</u> , Vol. 12, No. 3, pp. 587-601 (1983);
AC		Kim, J.S., et al., "Fabrication of Aluminum Oxide Thin Films by a Low-Pressure Metalorganic Chemical Vapor Deposition Technique", <u>App. Phys. Lett.</u> , 62(7), February 15, 1993;

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AP		Fournier, J., et al., "Preparation and Characterization of Thin Films of Alumina by Metal-Organic Chemical Vapor Deposition", <u>Mat. Res. Bull.</u> , Vol. 23, pp. 31-36, 1988;
AP		Klein, T.M., et al. "Evidence of Aluminum Silicate Formation During Chemical Vapor Deposition of Amorphous Al ₂ O ₃ Thin Films on Si (100)", <u>Applied Physics Letters</u> , Vol. 75, No. 25, pp. 4001-4003, 1999;

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AC		Lo, S.-H, et al., "Quantum-Mechanical Modelling of Electron Tunneling Current From the Inversion Layer of Ultra-Thin-Oxide nMOSFET's", <u>IEEE Electron Device Letters</u> , Vol. 18, No. 5, pp. 209-211, May 1997;
AC		Mutoh, H., et al., "Multilayer Metallization with Planar Interconnect Structure Utilizing CVD Al ₂ O ₃ Film", <u>J. Electrochem Soc.: SOLID-SCIENCE AND TECHNOLOGY</u> , Vol. 12, No. 7, pp. 987-992, July 1975; and

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Ac			Yom, S.S., et al., "Growth of γ -Al ₂ O ₃ Thin Films on Silicon by Low Pressure Metal-Organic Chemical Vapour Deposition", <u>Elsevier Sequoia</u> , 213, pp. 72-75, 1992.

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